MITSUBISHI IGBT Module

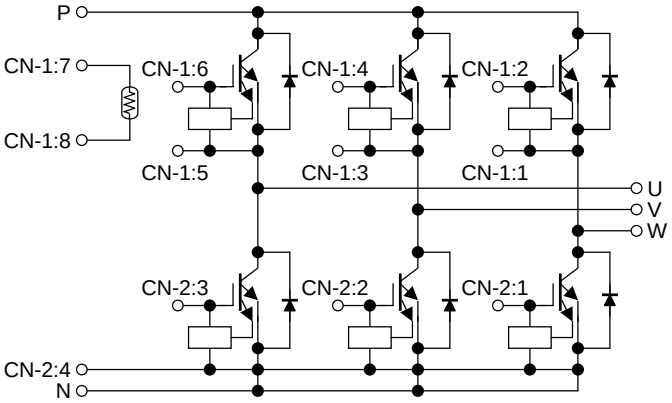
MG200J6ES61(600V/200A 6in1)

High Power Switching Applications

Motor Control Applications

- Integrates inverter power circuit in to a single package.
- The electrodes are isolated from case.
- Low thermal resistance
- $V_{CE\ (sat)}$ =2.0 V (typ.)

Equivalent Circuit



Signal Terminal

CN-1

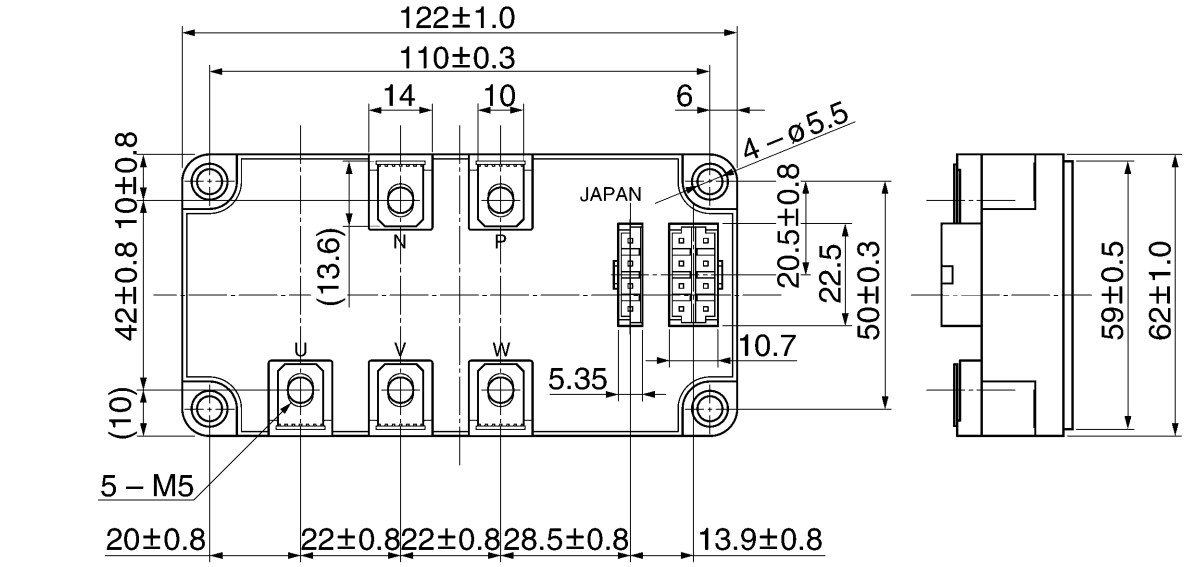
1.	E (W)	2.	G (W)	3.	E (V)	4.	G (V)
5.	E (U)	6.	G (U)	7.	TH1	8.	TH2

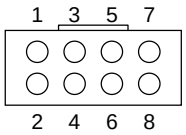
CN-2

1.	G (Z)	2.	G (Y)	3.	G (X)	4.	E (L)

Package Dimensions:

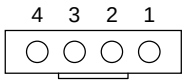
Unit: mm





CN-1

1.	E (W)	2.	G (W)	3.	E (V)	4.	G (V)
5.	E (U)	6.	G (U)	7.	TH1	8.	TH2



CN-2

1.	G (Z)	2.	G (Y)	3.	G (X)	4.	E (L)

Maximum Ratings (Ta = 25°C)

Stage	Characteristics		Symbol	Rating	Unit
Inverter	Collector-emitter voltage		V_{CES}	600	V
	Gate-emitter voltage		V_{GES}	±20	V
	Collector current	DC	I_C	200	A
		1 ms	I_{CP}	400	
	Forward current	DC	I_F	200	A
		1 ms	I_{FM}	400	
	Collector power dissipation (Tc = 25°C)		P_C	1000	W
Module	Junction temperature		T_j	150	°C
	Storage temperature range		T_{stg}	−40~125	°C
	Isolation voltage		V_{isol}	2500 (AC 1 min)	V
	Screw torque		—	3 (M5)	N·m

Electrical Characteristics (T_j = 25°C)

1. Inverter stage

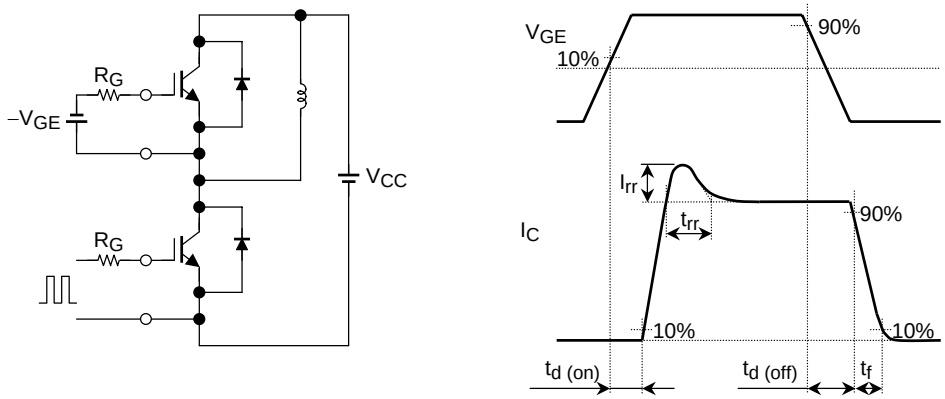
Characteristics		Symbol	Test Condition		Min	Typ.	Max	Unit
Gate leakage current		I_{GES}	V_{GE} = ±20 V, V_{CE} = 0		—	—	±500	nA
Collector cut-off current		I_{CES}	V_{CE} = 600 V, V_{GE} = 0		—	—	1.0	mA
Gate-emitter cut-off voltage		$V_{GE\ (off)}$	V_{CE} = 5 V, I_C = 200 mA		5.0	6.5	8.0	V
Collector-emitter saturation voltage		$V_{CE\ (sat)}$	V_{GE} = 15 V, I_C = 200 A	T_j = 25°C	—	2.0	2.4	V
				T_j = 125°C	—	—	2.6	
Input capacitance		C_{ies}	V_{CE} = 10 V, V_{GE} = 0, f = 1 MHz		—	40000	—	pF
Switching time	Turn-on delay time	$t_{d\ (on)}$	V_{CC} = 300 V, I_C = 200 A, V_{GE} = ±15 V, R_G = 10 Ω (Note 1)		—	—	1.00	μs
	Turn-off time	t_{off}			—	—	1.20	
	Fall time	t_f			—	—	0.50	
Reverse recovery time		t_{rr}			—	—	0.30	
Forward voltage		V_F	I_F = 200 A		—	2.2	2.6	V

Note 1: Switching time test circuit & timing chart

2. Module (Tc = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Zero-power resistance	R25	ITM = 0.2 mA	—	100	—	kΩ
B value	B25/85	Tc = 25°C/Tc = 85°C	—	4390	—	K
Junction to case thermal resistance	$R_{th\ (j-c)}$	Inverter IGBT stage	—	—	0.125	°C/W
		Inverter FRD stage	—	—	0.195	
Case to fin thermal resistance	$R_{th\ (c-f)}$	—	—	0.013	—	°C/W

Switching Time Test Circuit & Timing Chart



Recommneded conditions for application

Characteristics	Symbol	Min	Typ.	Max	Unit
P-N power terminal supply voltage	V_{CC}	—	300	400	V
Gate voltage	V_{GE}	13.5	15	16.5	V
Switching frequency	fc	—	—	20	kHz